



1.2W S/C-Band Power Amplifier

3.0-6.0 GHz

Preliminary Information

MAAPGM0022-DIE

Features

- ◆ 3.0-6.0 GHz Operation
- ◆ 1 Watt Saturated Output Power Level
- ◆ Variable Drain Voltage (4-10V) Operation
- ◆ Self-Aligned MSAG[®] MESFET Process

Primary Applications

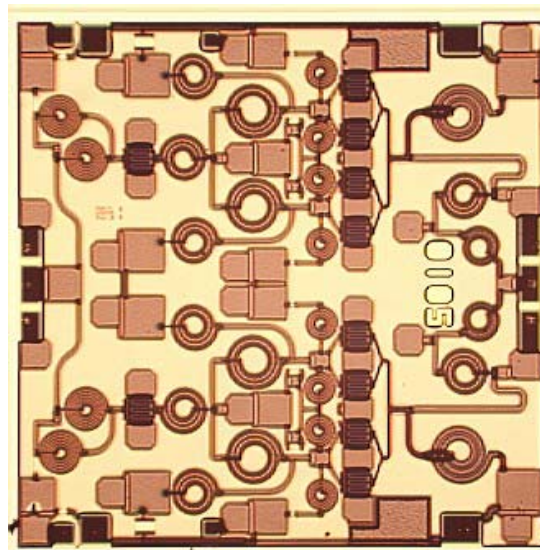
- ◆ 3.4-3.6 GHz WLL
- ◆ 3.7-4.2 GHz SatCom
- ◆ 5.1-5.9 GHz HyperLAN
- ◆ 5.8GHz ISM, RADAR

Description

The MAAPGM0022-Die is a 2-stage 1.2 W power amplifier with on-chip bias networks. This product is fully matched to 50 ohms on both the input and output. It can be used as a power amplifier stage or as a driver stage in high power applications.

Each device is 100% RF tested on wafer to ensure performance compliance. The part is fabricated using M/A-COM's repeatable, high performance and highly reliable GaAs Multifunction Self-Aligned Gate (MSAG[®]) MESFET Process. This process features silicon nitride passivation and polyimide scratch protection.

3.0-6.0 GHz GaAs MMIC Amplifier



Electrical Characteristics: $T_B = 40^\circ\text{C}^1$, $Z_0 = 50\ \Omega$, $V_{DD} = 8\text{V}$, $V_{GG} = -2\text{V}$, $P_{in} = 20\text{ dBm}$

Parameter	Symbol	Typical	Units
Bandwidth	f	3.0-6.0	GHz
Output Power	P_{OUT}	31	dBm
Power Added Efficiency	PAE	27	%
1-dB Compression Point	P_{1dB}	31	dBm
Small Signal Gain	G	17	dB
Input VSWR	VSWR	1.5:1	
Gate Current	I_{GG}	< 12	mA
Drain Current	I_{DD}	< 900	mA
Output Third Order Intercept	OTOI	43	dBm
Noise Figure	NF	6	dB
2 nd Harmonic	2f	-10	dBc
3 rd Harmonic	3f	-20	dBc

1. T_B = MMIC Base Temperature

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Maximum Operating Conditions ¹

Parameter	Symbol	Absolute Maximum	Units
Input Power	P _{IN}	25.0	dBm
Drain Supply Voltage	V _{DD}	+12.0	V
Gate Supply Voltage	V _{GG}	-3.0	V
Quiescent Drain Current (No RF)	I _{DQ}	950	mA
Quiescent Power Dissipated (No RF)	P _{DISS}	6.3	W
Junction Temperature	T _J	180	°C
Storage Temperature	T _{STG}	-55 to +150	°C

1. Operation outside of these ranges may reduce product reliability. Operation at other than the typical values may result in performance outside the guaranteed limits.

Recommended Operating Conditions

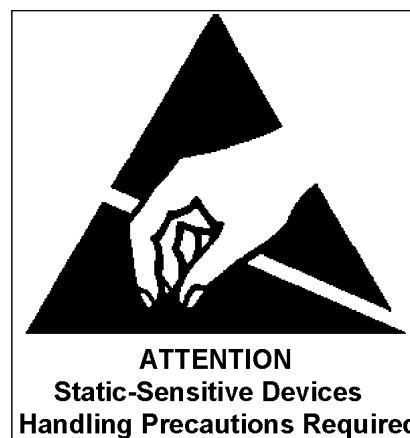
Characteristic	Symbol	Min	Typ	Max	Unit
Drain Voltage	V _{DD}	4.0	8.0	10.0	V
Gate Voltage	V _{GG}	-2.3	-2.0	-1.5	V
Input Power	P _{IN}			23.0	dBm
Junction Temperature	T _J			150	°C
MMIC Base Temperature	T _B			Note 2	°C

2. Maximum MMIC Base Temperature = 150°C — 12.7 °C/W * V_{DD} * I_{DQ}

Operating Instructions

This device is static sensitive. Please handle with care. To operate the device, follow these steps.

1. Apply V_{GG} = -2 V, V_{DD} = 0 V.
2. Ramp V_{DD} to desired voltage, typically 8 V.
3. Adjust V_{GG} to set I_{DQ}, (approximately @ -2 V).
4. Set RF input.
5. Power down sequence in reverse. Turn gate voltage off last.



Specifications subject to change without notice.

Customer Service: Tel. (888)-563-3949

Email: macom_adbu_ics@tycoelectronics.com

■ **North America:** Tel. (800) 366-2266

■ **Asia/Pacific:** Tel. +81-44-844-8296, Fax +81-44-844-8298

■ **Europe:** Tel. +44 (1344) 869 595, Fax +44 (1344) 300 020

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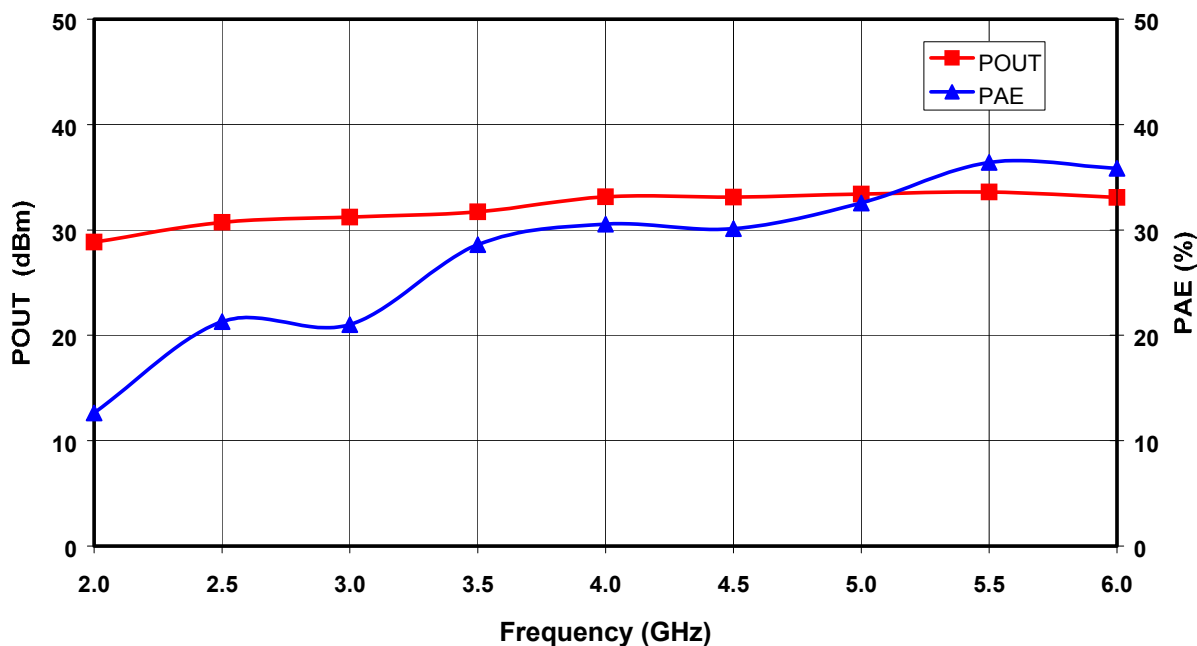


Figure 1. Output Power and Power Added Efficiency vs. Frequency at $V_{DD} = 8V$ and $P_{in} = 20$ dBm.

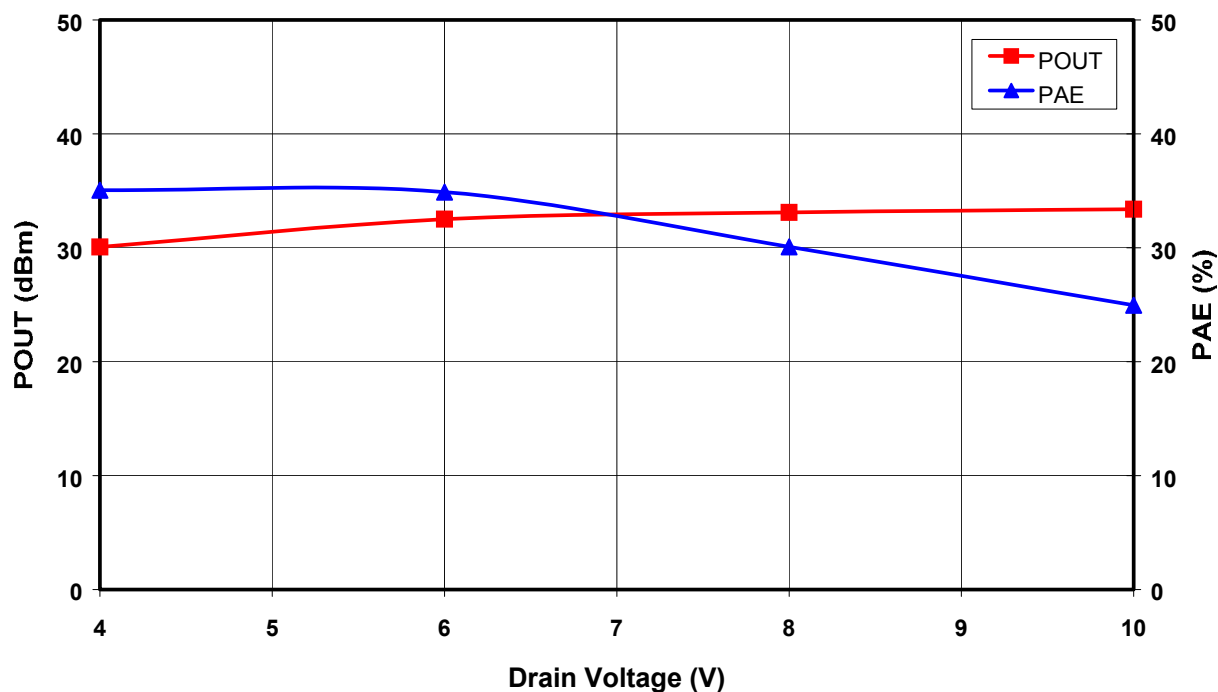


Figure 2. Saturated Output Power and Power Added Efficiency vs. Drain Voltage at $f_0 = 4.5$ GHz.

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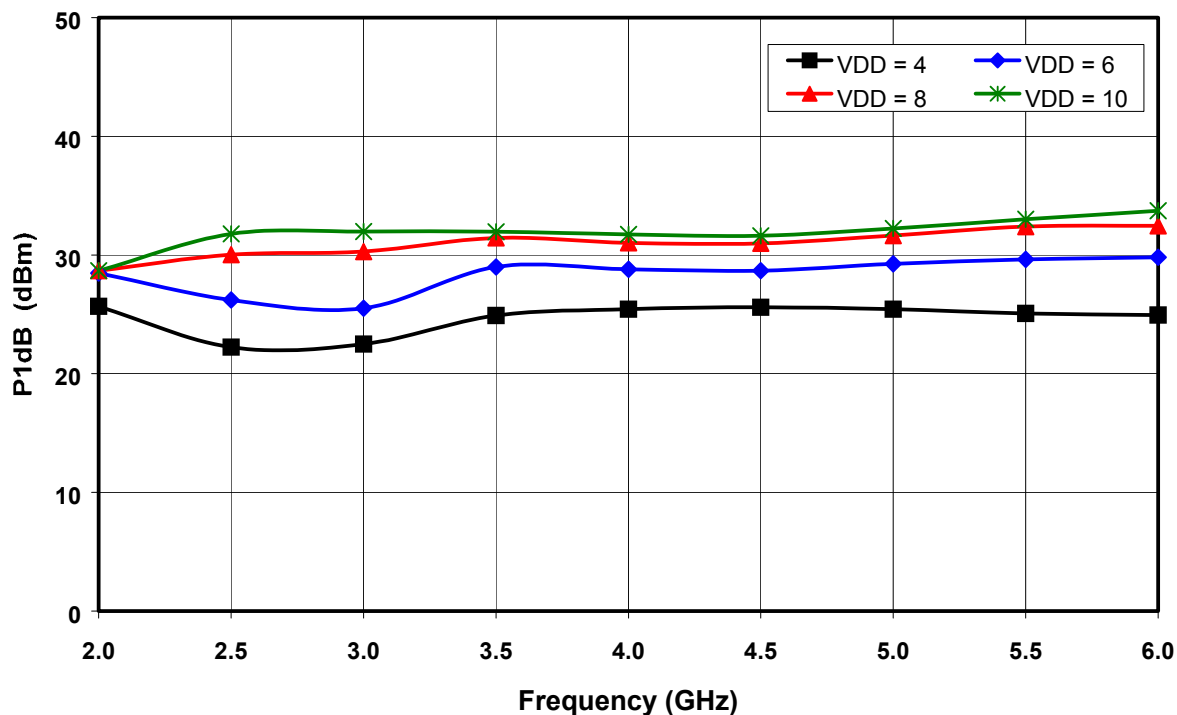
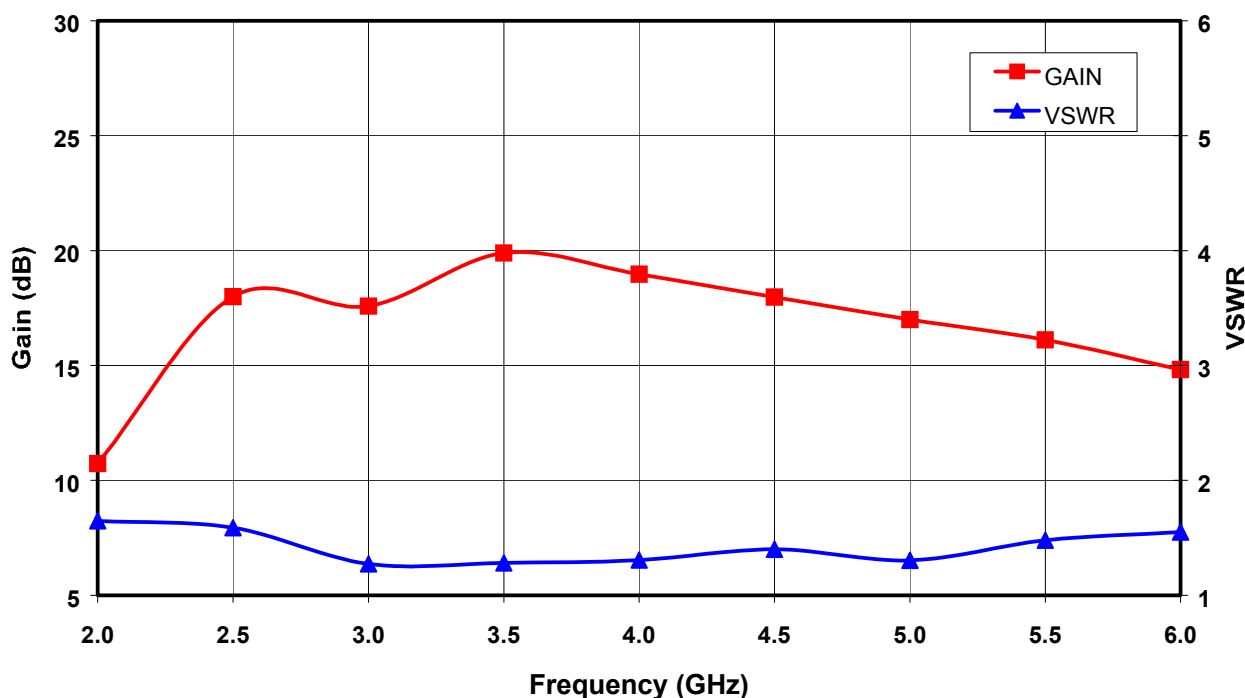


Figure 3. 1dB Compression Point vs. Drain Voltage

Figure 4. Small Signal Gain and Input VSWR vs. Frequency at $V_{DD} = 8V$.

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Chip Size: 2.980 x 2.980 x 0.075 mm (117 x 117 x 3 mils)



Bond Pad Dimensions

Pad	Size (μm)	Size (mils)
RF In and Out	100 x 200	4 x 8
DC Drain Supply Voltage VDD	200 x 150	8 x 6
DC Gate Supply Voltage VGG	150 x 150	6 x 6

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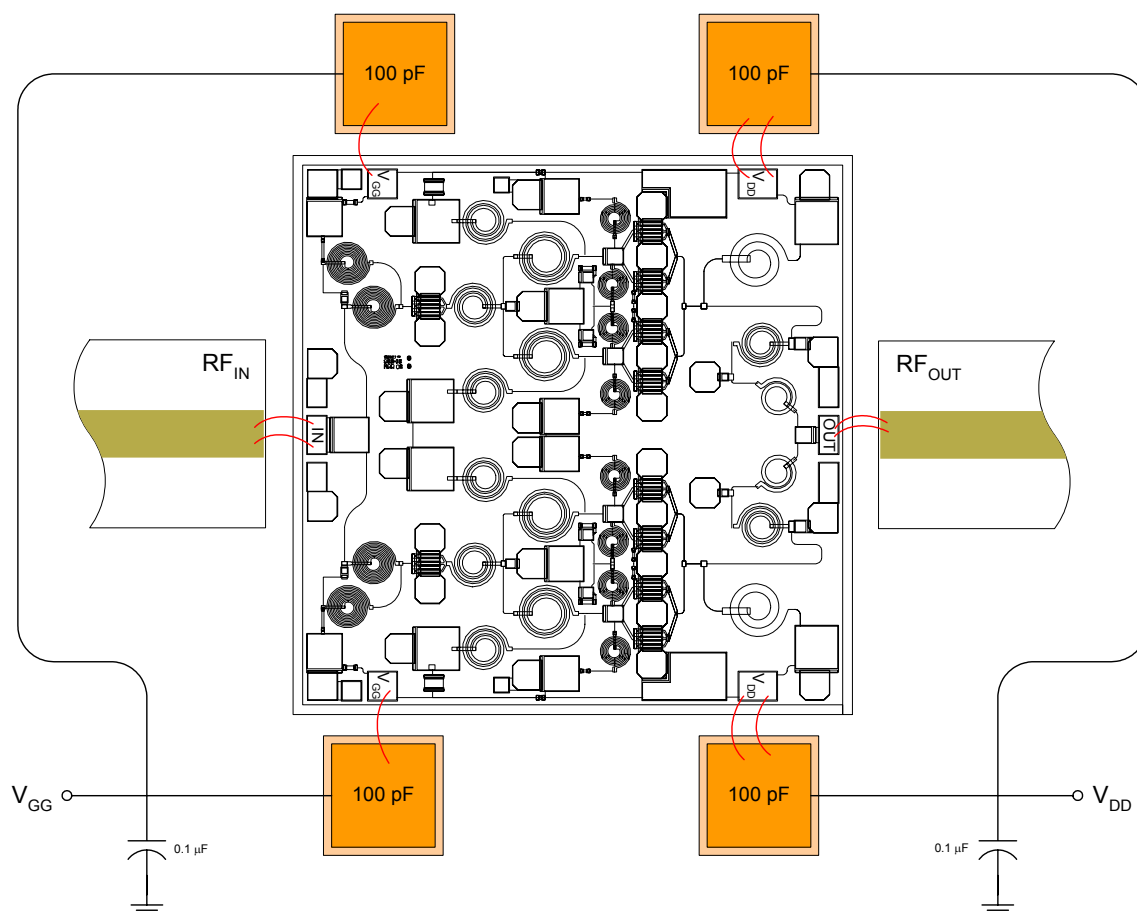


Figure 6. Recommended bonding diagram for pedestal mount.
Support circuitry typical of MMIC characterization fixture for CW testing.

Assembly Instructions:

Die attach: Use AuSn (80/20) 1-2 mil. preform solder. Limit time @ 300 °C to less than 5 minutes.

Wirebonding: Bond @ 160 °C using standard ball or thermal compression wedge bond techniques. For DC pad connections, use either ball or wedge bonds. For best RF performance, use wedge bonds of shortest length, although ball bonds are also acceptable.

Biasing Note: Must apply negative bias to V_{GG} before applying positive bias to V_{DD} to prevent damage to amplifier.

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